

EAST - (10785310 trench NROM wsp.1)

File View Edit Tools Window Help

Active

- L1: (1158381) (nrom read adj only adj memory)
- L2: (11) 10/785310
- L3: (231318) (sonos monos mnos nrom nitride adj) memory
- L4: (771) (nrom)
- L5: (1990) (nonvolatile non adj volatile adj read adj only)
- L6: (71) 4 with 5
- L7: (1832) (nrom nitride adj read adj only adj memory)
- L8: (1391) (nitride adj read adj only adj memory)
- L9: (1392) (nitride adj read adj only)
- L10: (1322) 8 with 4
- L11: (88825) trench\$3
- L12: (833) 8 4
- L13: (32) 11 with 12
- L14: (146) 11 same 12
- L15: (785282) (select\$4 side control adj (gate line) \$6
- L16: (171) 14 and 15
- L17: (168) 11 and 12
- L18: (684496) (select\$4 side 1 adj (gate line) \$6
- L19: (68) 17 and 18
- L20: (1251684) group\$3
- L21: (21) 12 with 20
- L22: (2) 12 same 20
- L23: (553) nor adj memory
- L24: (4) 23 with 11
- L25: (15) 23 same 11

23 same 11

April 2005

#	Inventor	Document	Issued	Title	Current	Current	Retrieval	S	C	P	Image	Def
1	Ding, Yi	US 200500	2005	3	Fabrication of conductive gates for non	438/25	438/268					US 20050
2	Ding, Yi	US 200402	2004	3	Fabrication of dielectric on a gate surf	438/58	438/197					US 20040
3	Ding, Yi	US 200402	2004	3	FABRICATION OF GATE DIELECTRIC IN NONV	438/25						US 20040
4	Ding, Yi	US 200402	2004	3	FABRICATION OF GATE DIELECTRIC IN NONV	257/31						US 20040
5	Ding, Yi	US 200402	2004	61	NONVOLATILE MEMORIES WITH A FLOATING	257/31	257/318					US 20040
6	Ding, Yi	US 2004018	2004	47	Nonvolatile memories and methods of	438/25	438/258					US 200401
7	Ding, Yi	US 2004018	2004	5	Nonvolatile memories and methods of	438/25	257/316					US 200401
8	Ding, Yi	US 2004018	2004	4	Fabrication of integrated circuit eleme	438/25						US 200401
9	Forbes, Leo	US 200302	2003	2	Nor flash memory cell with high storag	365/18						US 20030
10	Li Chi Han B	US 200201	2002	11	Non-volatile memory with a serial tran	257/29	257/127.10					US 200201

✓ No Code [No WINC]

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